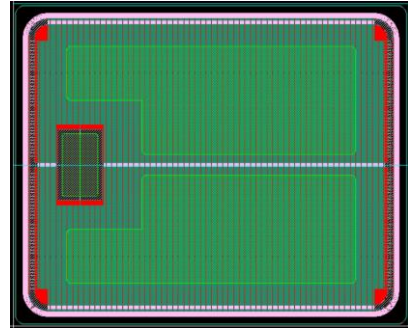


IV2Q12040BD – 1200V 40mΩ Gen2 SiC MOSFET Chip

Features

- 2nd Generation SiC MOSFET Technology with +15~+18V gate drive
- High blocking voltage with low on-resistance
- High speed switching with low capacitance
- 175°C operating junction temperature capability
- Ultra fast and robust intrinsic body diode

Chip Outline:



Applications

- EV chargers and OBCs
- Solar boosters
- Automotive compressor inverters
- AC/DC power supplies

Part Number	Die Size
IV2Q12040BD	Please contact your sales representative to get the detailed die information

Absolute Maximum Ratings (T_c=25°C unless otherwise specified)

Symbol	Parameter	Value	Unit	Test Conditions	Note
V _{DS}	Drain-Source voltage	1200	V	V _{GS} =0V, I _D =100μA	
V _{GSmax} (Transient)	Maximum transient voltage	-10 to 23	V	Duty cycle<1%, and pulse width<200ns	
V _{GSon}	Recommended turn-on voltage	15 to 18	V		
V _{GSoff}	Recommended turn-off voltage	-5 to -2	V	Typical -3.5V	
I _D	Drain current (continuous)	65	A	V _{GS} =18V, T _c =25°C	Fig. 23
		48	A	V _{GS} =18V, T _c =100°C	
I _{DM}	Drain current (pulsed)	162	A	Pulse width limited by SOA and dynamic R _{θ(j-c)}	Fig. 25, 26
I _{SM}	Body diode current (pulsed)	162	A	Pulse width limited by SOA and dynamic R _{θ(j-c)}	Fig. 25, 26
P _{TOT}	Total power dissipation	375	W	T _c =25°C	Fig. 24
T _{stg}	Storage temperature range	-55 to 175	°C		
T _J	Operating junction temperature	-55 to 175	°C		
T _L	Solder Temperature	260	°C	wave soldering only allowed at leads, 1.6mm from case for 10 s	

Note1: Assumes R_{θ(j-c)}< 0.4°C/W.

Note2: All the electrical data and curve data please refer to datasheet for packaged device which part number is IV2Q12040T4Z.

Electrical Characteristics ($T_c=25^\circ\text{C}$ unless otherwise specified)

Symbol	Parameter	Value			Unit	Test Conditions	Note
		Min.	Typ.	Max.			
I_{DSS}	Zero gate voltage drain current		5	100	μA	$V_{DS}=1200\text{V}, V_{GS}=0\text{V}$	
I_{GSS}	Gate leakage current			± 100	nA	$V_{DS}=0\text{V}, V_{GS}=-5\sim 20\text{V}$	
V_{TH}	Gate threshold voltage	1.8	2.8	4.5	V	$V_{GS}=V_{DS}, I_D=9\text{mA}$	Fig. 8, 9
			2.1			$V_{GS}=V_{DS}, I_D=9\text{mA}$ @ $T_J=175^\circ\text{C}$	
R_{ON}	Static drain-source on-resistance		40	52	$\text{m}\Omega$	$V_{GS}=18\text{V}, I_D=20\text{A}$ @ $T_J=25^\circ\text{C}$	Fig. 4, 5, 6, 7
			75		$\text{m}\Omega$	$V_{GS}=18\text{V}, I_D=20\text{A}$ @ $T_J=175^\circ\text{C}$	
			50	65	$\text{m}\Omega$	$V_{GS}=15\text{V}, I_D=20\text{A}$ @ $T_J=25^\circ\text{C}$	
			80		$\text{m}\Omega$	$V_{GS}=15\text{V}, I_D=20\text{A}$ @ $T_J=175^\circ\text{C}$	
C_{iss}	Input capacitance		2160		pF	$V_{DS}=800\text{V}, V_{GS}=0\text{V},$ $f=1\text{MHz}, V_{AC}=25\text{mV}$	Fig. 16
C_{oss}	Output capacitance		100		pF		
C_{rss}	Reverse transfer capacitance		5.8		pF		
E_{oss}	C_{oss} stored energy		40		μJ		Fig. 17
Q_g	Total gate charge		110		nC	$V_{DS}=800\text{V}, I_D=30\text{A},$ $V_{GS}=-3$ to 18V	Fig. 18
Q_{gs}	Gate-source charge		25		nC		
Q_{gd}	Gate-drain charge		59		nC		
R_g	Gate input resistance		2.1		Ω	$f=1\text{MHz}$	
E_{ON}	Turn-on switching energy		446.3		μJ	$V_{DS}=800\text{V}, I_D=30\text{A},$ $V_{GS}=-3.5$ to $18\text{V},$ $R_{G(\text{ext})}=3.3\Omega,$ $L=200\mu\text{H}$ $T_J=25^\circ\text{C}$	Fig. 19, 20
E_{OFF}	Turn-off switching energy		70.0		μJ		
$t_{d(\text{on})}$	Turn-on delay time		9.6		ns		
t_r	Rise time		22.1				
$t_{d(\text{off})}$	Turn-off delay time		19.3				
t_f	Fall time		10.5				
E_{ON}	Turn-on switching energy		644.4		μJ	$V_{DS}=800\text{V}, I_D=30\text{A},$ $V_{GS}=-3.5$ to $18\text{V},$ $R_{G(\text{ext})}=3.3\Omega, L=200\mu\text{H}$ $T_J=175^\circ\text{C}$	Fig. 22
E_{OFF}	Turn-off switching energy		73.8		μJ		

Reverse Diode Characteristics ($T_c=25^\circ\text{C}$ unless otherwise specified)

Symbol	Parameter	Value			Unit	Test Conditions	Note
		Min.	Typ.	Max.			
V_{SD}	Diode forward voltage		4.2		V	$I_{SD}=20\text{A}, V_{GS}=0\text{V}$	Fig. 10, 11, 12
			4.0		V	$I_{SD}=20\text{A}, V_{GS}=0\text{V}, T_J=175^\circ\text{C}$	
I_S	Diode forward current (continuous)			63	A	$V_{GS}=-2\text{V}, T_c=25^\circ\text{C}$	
				36	A	$V_{GS}=-2\text{V}, T_c=100^\circ\text{C}$	
t_{rr}	Reverse recovery time		42.0		ns	$V_{GS}=-3.5\text{V}/+18\text{V}, I_{SD}=30\text{A}, V_R=800\text{V}, R_{G(\text{ext})}=10\Omega, L=200\mu\text{H}, di/dt=3000\text{A}/\mu\text{s}$	
Q_{rr}	Reverse recovery charge		198.1		nC		
I_{RRM}	Peak reverse recovery current		17.4		A		

Typical Performance (curves)

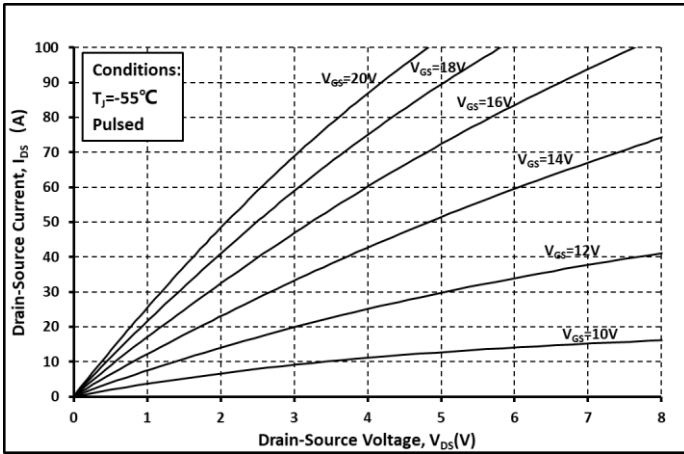


Fig. 1 Output Curve @ $T_j = -55^\circ\text{C}$

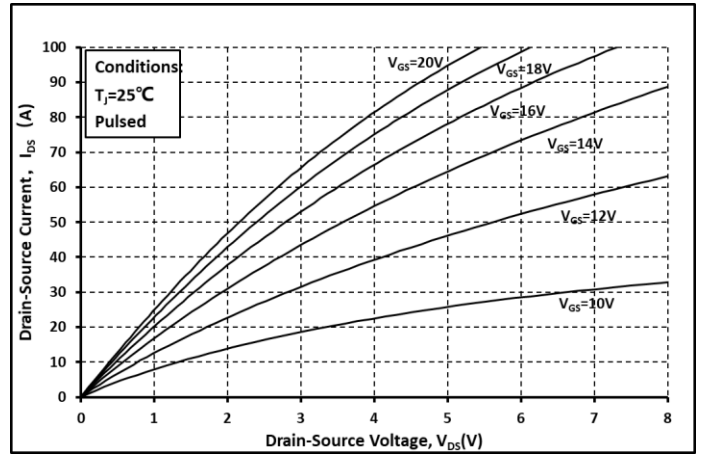


Fig. 2 Output Curve @ $T_j = 25^\circ\text{C}$

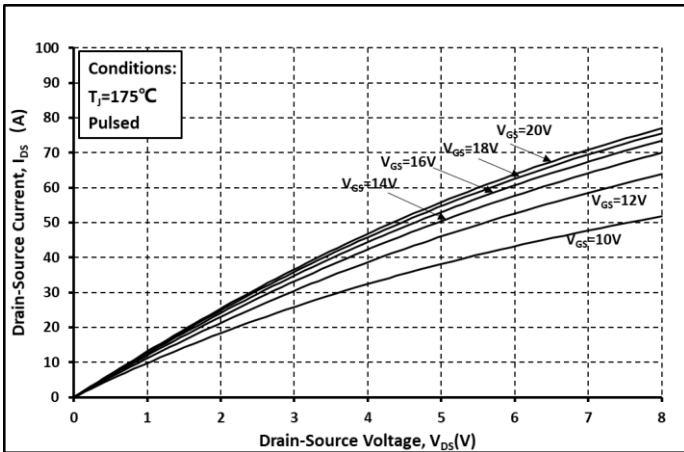


Fig. 3 Output Curve @ $T_j = 175^\circ\text{C}$

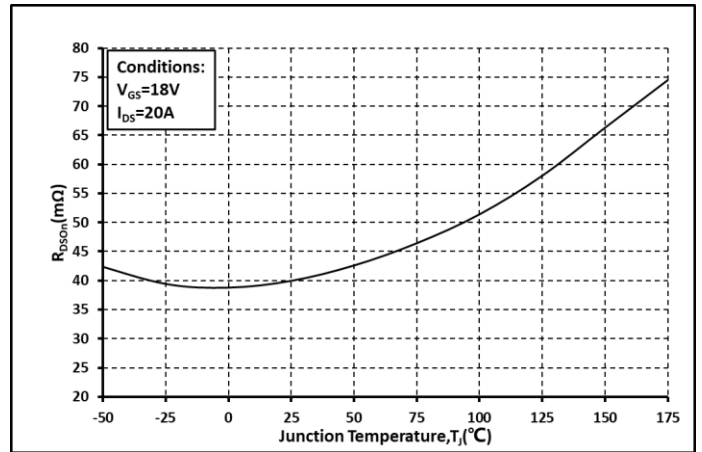


Fig. 4 $R_{DS(on)}$ vs. Temperature

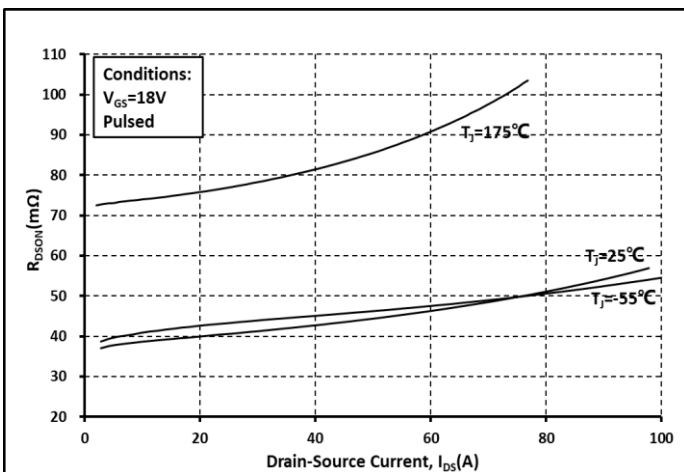


Fig. 5 $R_{DS(on)}$ vs. I_{DS} @ Various Temperature

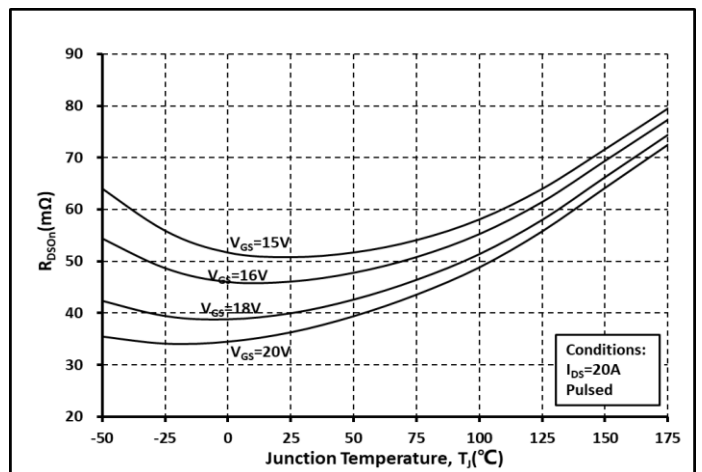


Fig. 6 $R_{DS(on)}$ vs. Temperature @ Various V_{GS}

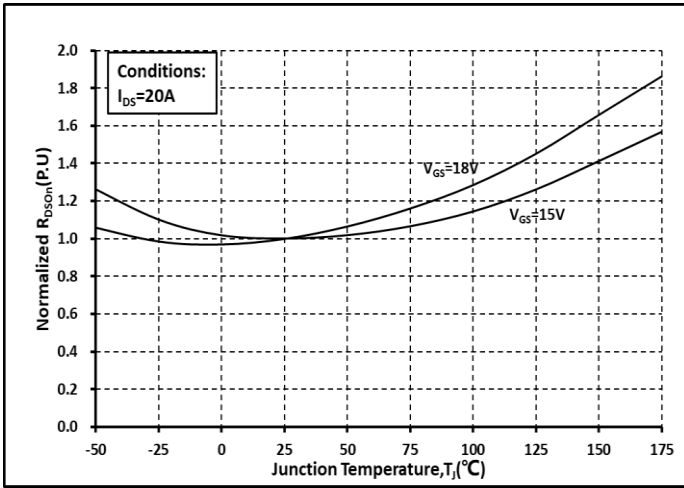


Fig. 7 Normalized Ron vs. Temperature

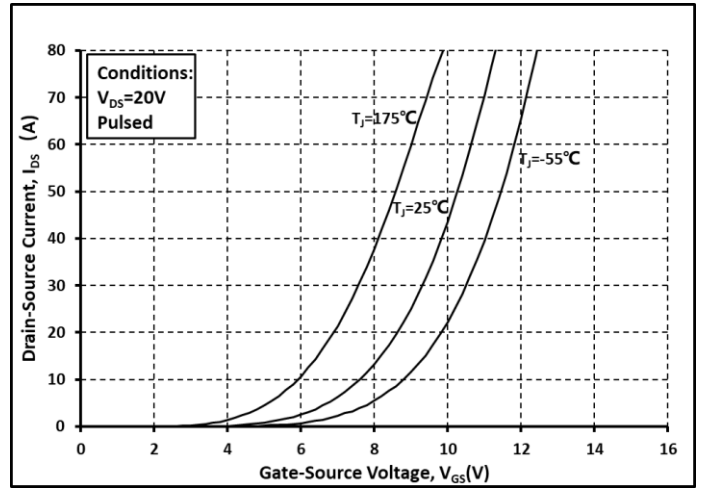


Fig. 8 Transfer Curves @ Various Temperature

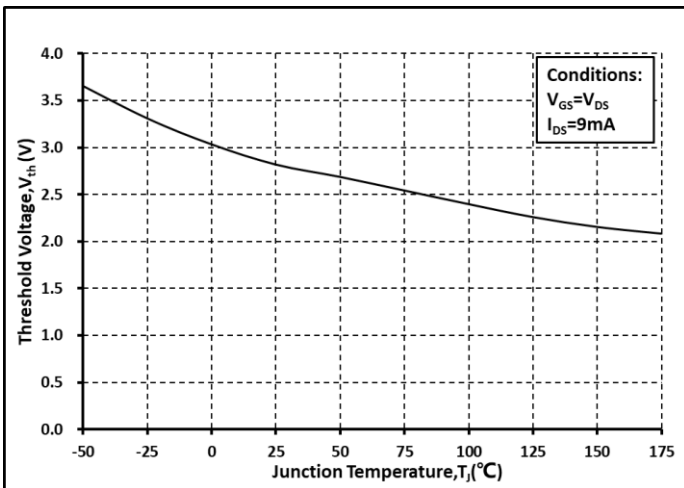


Fig. 9 Threshold Voltage vs. Temperature

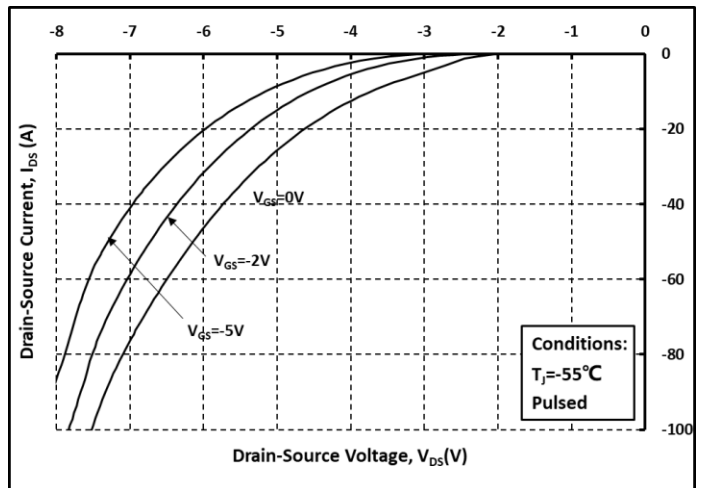


Fig. 10 Body Diode curves @ $T_j = -55^\circ\text{C}$

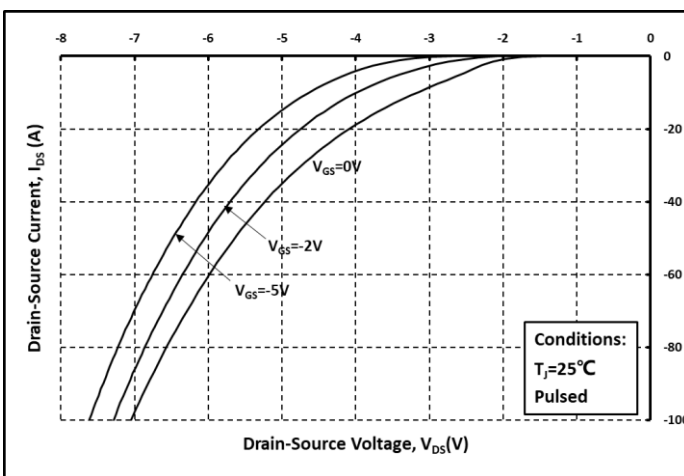


Fig. 11 Body Diode curves @ $T_j = 25^\circ\text{C}$

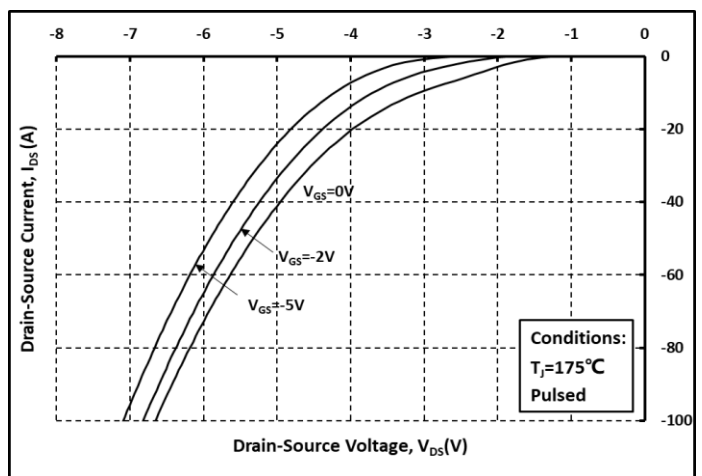


Fig. 12 Body Diode curves @ $T_j = 175^\circ\text{C}$

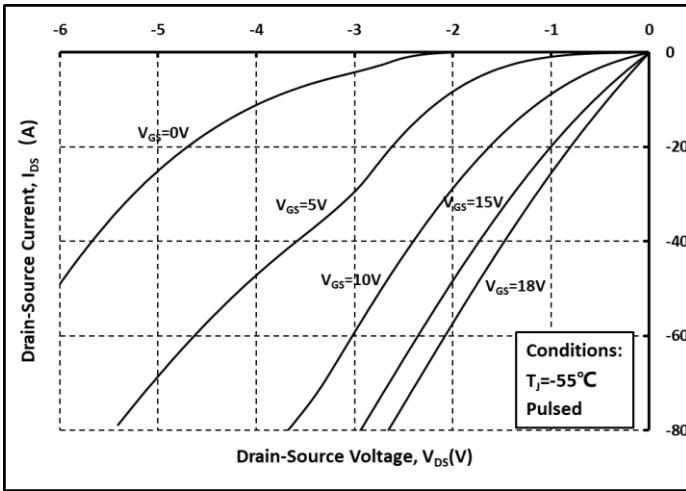


Fig. 13 3rd Quadrant curves @ $T_j = -55^\circ\text{C}$

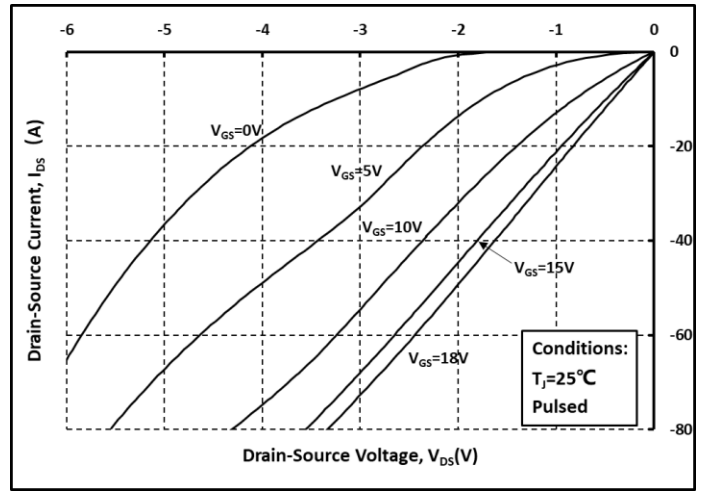


Fig. 14 3rd Quadrant curves @ $T_j = 25^\circ\text{C}$

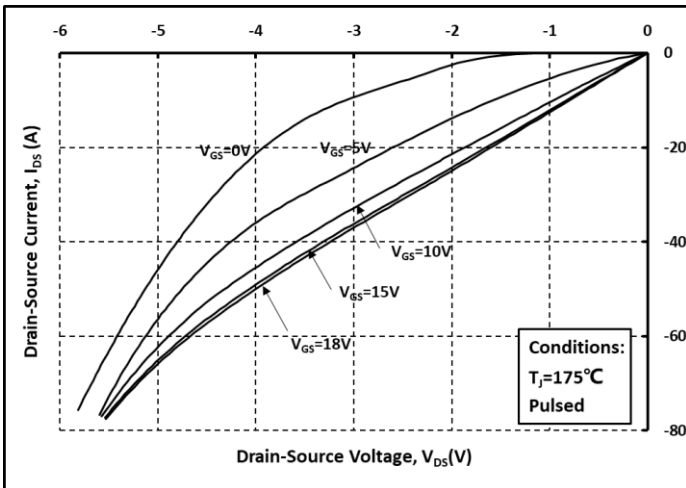


Fig. 15 3rd Quadrant curves @ $T_j = 175^\circ\text{C}$

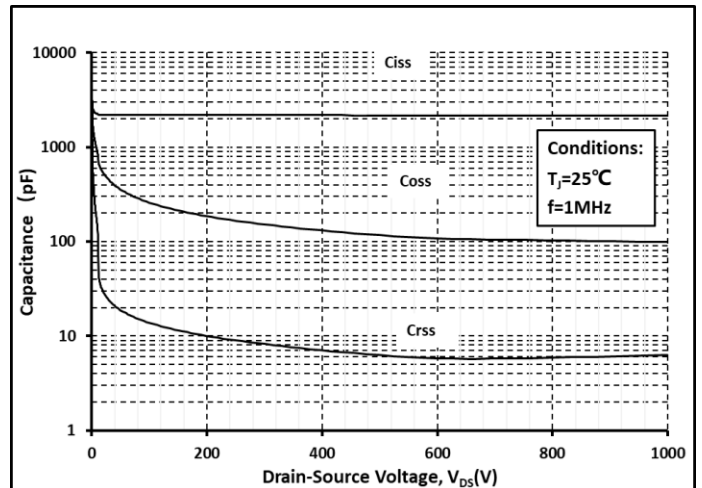


Fig. 16 Capacitance vs. V_{DS}

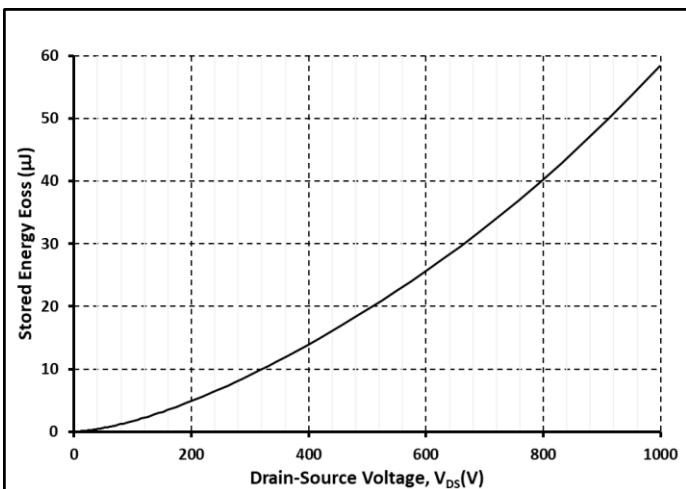


Fig. 17 Output Capacitor Stored Energy

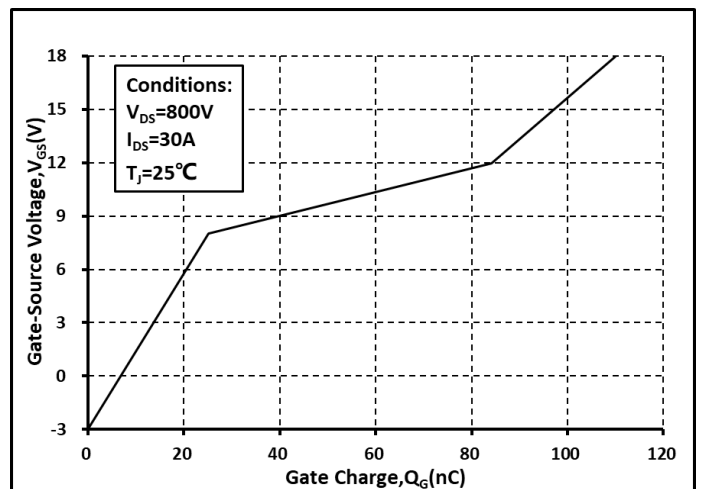


Fig. 18 Gate Charge Characteristics

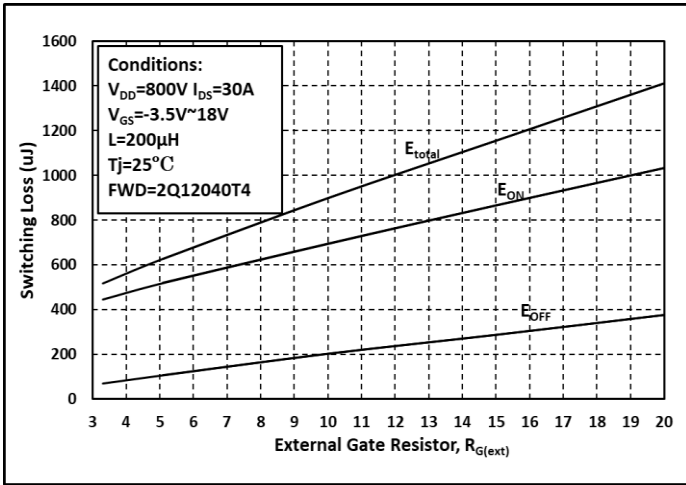


Fig. 19 Switching Energy vs. $R_{G(ext)}$

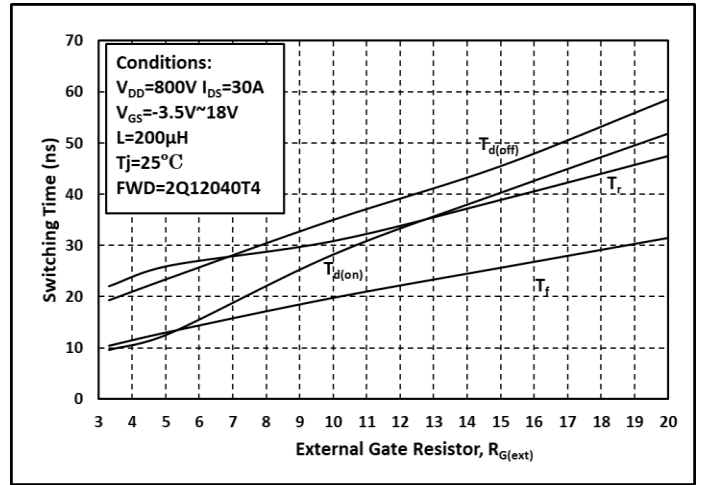


Fig. 20 Switching Times vs. $R_{G(ext)}$

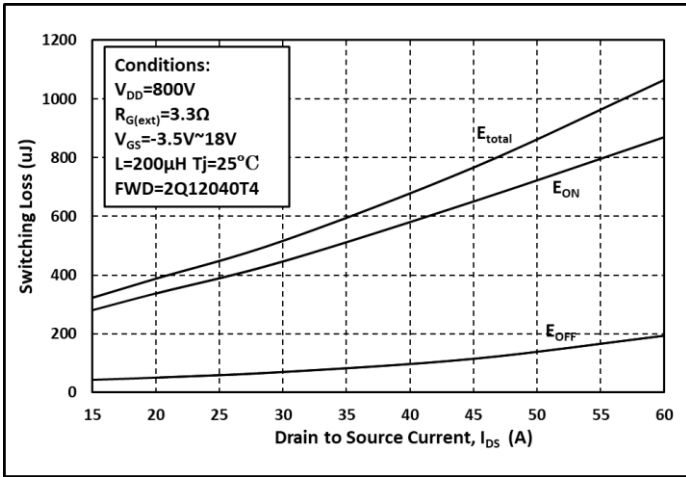


Fig. 21 Switching Energy vs. I_{DS}

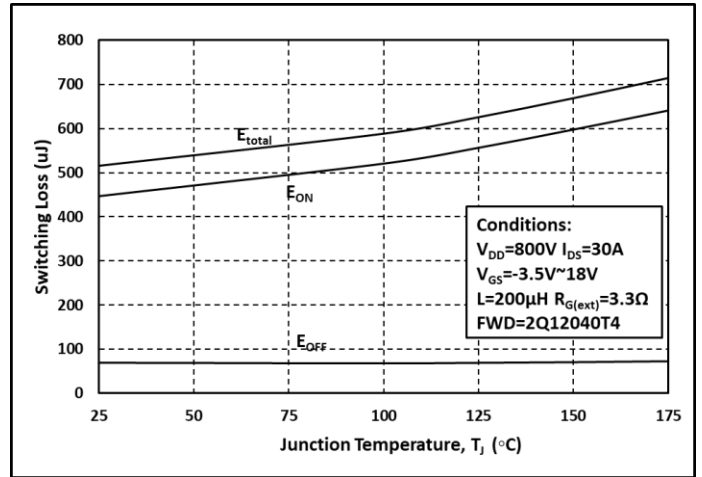


Fig. 22 Switching Energy vs. Temperature

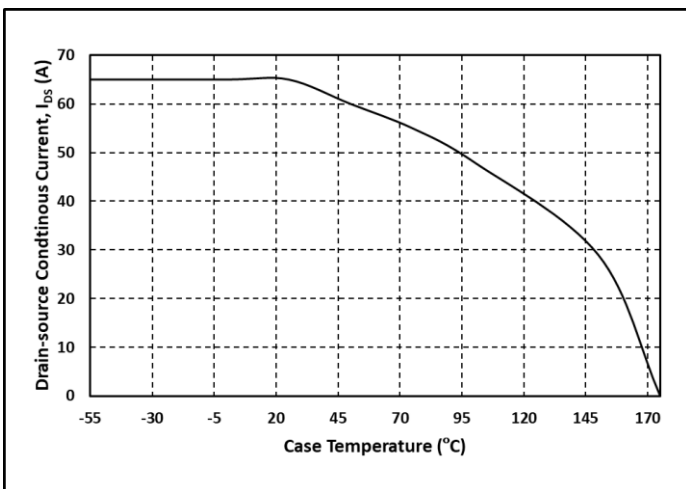


Fig. 23 Continuous Drain Current vs. Case Temperature

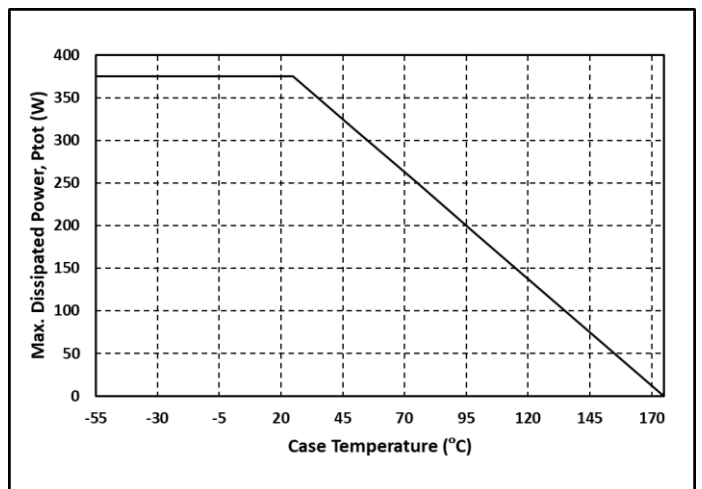


Fig. 24 Max. Power Dissipation Derating vs. Case Temperature

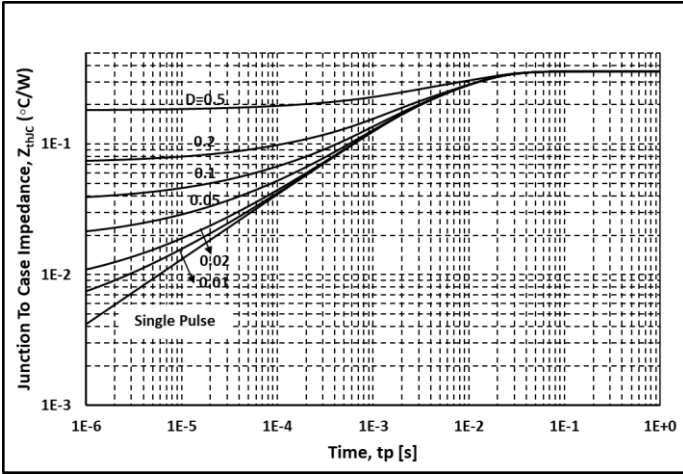


Fig. 25 Thermal impedance

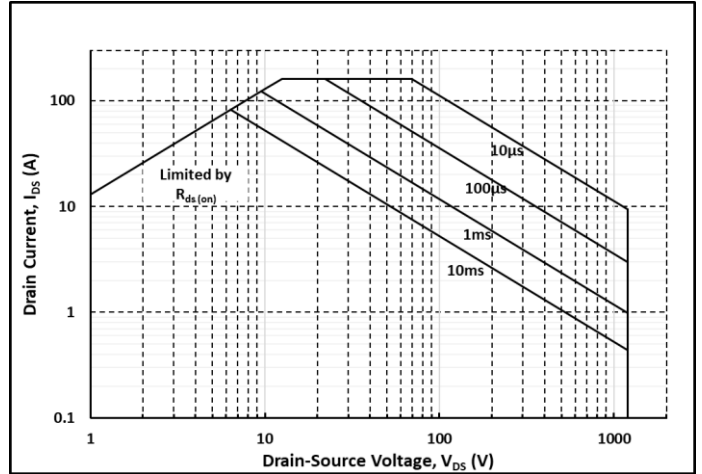


Fig. 26 Safe Operating Area

Notes

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